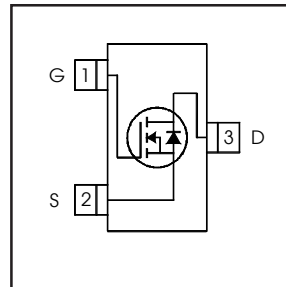


IRLML2803GPbF

HEXFET® Power MOSFET

- Generation V Technology
- Ultra Low On-Resistance
- N-Channel MOSFET
- SOT-23 Footprint
- Low Profile (<1.1mm)
- Available in Tape and Reel
- Fast Switching
- Lead-Free
- Halogen-Free



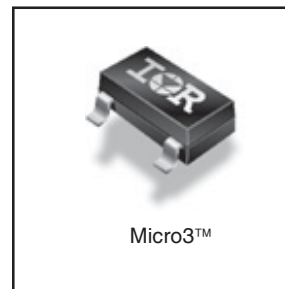
$V_{DSS} = 30V$

$R_{DS(on)} = 0.25\Omega$

Description

Fifth Generation HEXFETs from International Rectifier utilize advanced processing techniques to achieve extremely low on-resistance per silicon area. This benefit, combined with the fast switching speed and ruggedized device design that HEXFET Power MOSFETs are well known for, provides the designer with an extremely efficient and reliable device for use in a wide variety of applications.

A customized leadframe has been incorporated into the standard SOT-23 package to produce a HEXFET Power MOSFET with the industry's smallest footprint. This package, dubbed the Micro3, is ideal for applications where printed circuit board space is at a premium. The low profile (<1.1mm) of the Micro3 allows it to fit easily into extremely thin application environments such as portable electronics and PCMCIA cards.



Absolute Maximum Ratings

| | Parameter | Max. | Units |
|----------------------------|--|--------------|-------|
| I_D @ $T_A = 25^\circ C$ | Continuous Drain Current, $V_{GS} @ 10V$ | 1.2 | A |
| I_D @ $T_A = 70^\circ C$ | Continuous Drain Current, $V_{GS} @ 10V$ | 0.93 | |
| I_{DM} | Pulsed Drain Current ① | 7.3 | |
| P_D @ $T_A = 25^\circ C$ | Power Dissipation | 540 | mW |
| | Linear Derating Factor | 4.3 | mW/°C |
| V_{GS} | Gate-to-Source Voltage | ± 20 | V |
| E_{AS} | Single Pulse Avalanche Energy ⑤ | 3.9 | mJ |
| dv/dt | Peak diode Recovery dv/dt ② | 5.0 | V/ns |
| T_J, T_{STG} | Junction and Storage Temperature Range | -55 to + 150 | °C |

Thermal Resistance

| | Parameter | Typ. | Max. | Units |
|-----------------|-------------------------------|------|------|-------|
| $R_{\theta JA}$ | Maximum Junction-to-Ambient ④ | — | 230 | °C/W |

Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

| | Parameter | Min. | Typ. | Max. | Units | Conditions |
|--|--------------------------------------|------|-------|------|-------|---|
| V _{(BR)DSS} | Drain-to-Source Breakdown Voltage | 30 | — | — | V | V _{GS} = 0V, I _D = 250μA |
| ΔV _{(BR)DSS} /ΔT _J | Breakdown Voltage Temp. Coefficient | — | 0.029 | — | V/°C | Reference to 25°C, I _D = 1mA |
| R _{DS(on)} | Static Drain-to-Source On-Resistance | — | — | 0.25 | Ω | V _{GS} = 10V, I _D = 0.91A ③ |
| | | — | — | 0.40 | | V _{GS} = 4.5V, I _D = 0.46A ③ |
| V _{GS(th)} | Gate Threshold Voltage | 1.0 | — | — | V | V _{DS} = V _{GS} , I _D = 250μA |
| g _{fs} | Forward Transconductance | 0.87 | — | — | S | V _{DS} = 10V, I _D = 0.46A |
| I _{DSS} | Drain-to-Source Leakage Current | — | — | 1.0 | μA | V _{DS} = 24V, V _{GS} = 0V |
| | | — | — | 25 | | V _{DS} = 24V, V _{GS} = 0V, T _J = 125°C |
| I _{GSS} | Gate-to-Source Forward Leakage | — | — | -100 | nA | V _{GS} = -20V |
| | Gate-to-Source Reverse Leakage | — | — | 100 | | V _{GS} = 20V |
| Q _g | Total Gate Charge | — | 3.3 | 5.0 | nC | I _D = 0.91A |
| Q _{gs} | Gate-to-Source Charge | — | 0.48 | 0.72 | | V _{DS} = 24V |
| Q _{gd} | Gate-to-Drain ("Miller") Charge | — | 1.1 | 1.7 | | V _{GS} = 10V, See Fig. 6 and 9 ③ |
| t _{d(on)} | Turn-On Delay Time | — | 3.9 | — | | V _{DD} = 15V |
| t _r | Rise Time | — | 4.0 | — | ns | I _D = 0.91A |
| t _{d(off)} | Turn-Off Delay Time | — | 9.0 | — | | R _G = 6.2Ω |
| t _f | Fall Time | — | 1.7 | — | | R _D = 16Ω, See Fig. 10 ③ |
| C _{iss} | Input Capacitance | — | 85 | — | pF | V _{GS} = 0V |
| C _{oss} | Output Capacitance | — | 34 | — | | V _{DS} = 25V |
| C _{rss} | Reverse Transfer Capacitance | — | 15 | — | | f = 1.0MHz, See Fig. 5 |

Source-Drain Ratings and Characteristics

| | Parameter | Min. | Typ. | Max. | Units | Conditions |
|-----------------|---|------|------|------|-------|---|
| I _S | Continuous Source Current (Body Diode) | — | — | 0.54 | A | MOSFET symbol showing the integral reverse p-n junction diode. |
| I _{SM} | Pulsed Source Current (Body Diode) ① | — | — | 7.3 | | |
| V _{SD} | Diode Forward Voltage | — | — | 1.2 | V | T _J = 25°C, I _S = 0.91A, V _{GS} = 0V ③ |
| t _{rr} | Reverse Recovery Time | — | 26 | 40 | ns | T _J = 25°C, I _F = 0.91A |
| Q _{rr} | Reverse Recovery Charge | — | 22 | 32 | nC | di/dt = 100A/μs ③ |

Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature. (See fig. 11)
- ② I_{SD} ≤ 0.91A, di/dt ≤ 120A/μs, V_{DD} ≤ V_{(BR)DSS}, T_J ≤ 150°C
- ③ Pulse width ≤ 300μs; duty cycle ≤ 2%.
- ④ Surface mounted on FR-4 board, t ≤ 5sec.
- ⑤ Limited by T_{Jmax}, starting T_J = 25°C, L = 9.4mH, R_G = 25Ω, I_{AS} = 0.9A.

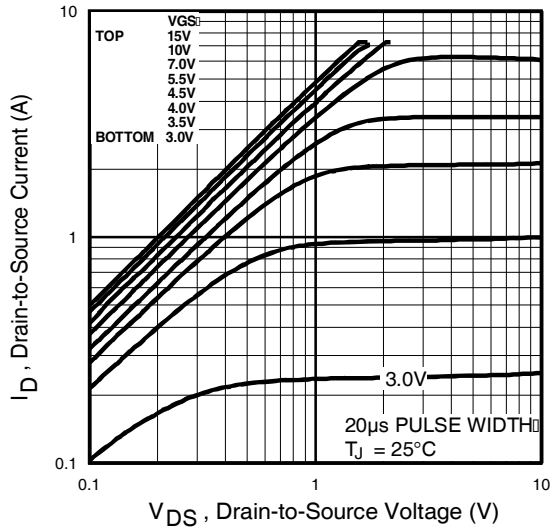


Fig 1. Typical Output Characteristics

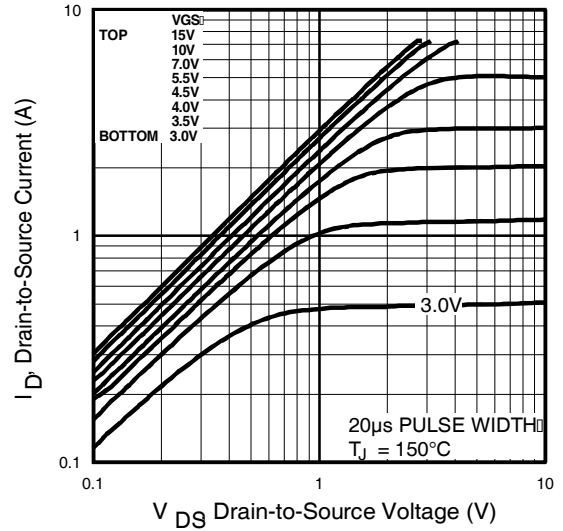


Fig 2. Typical Output Characteristics

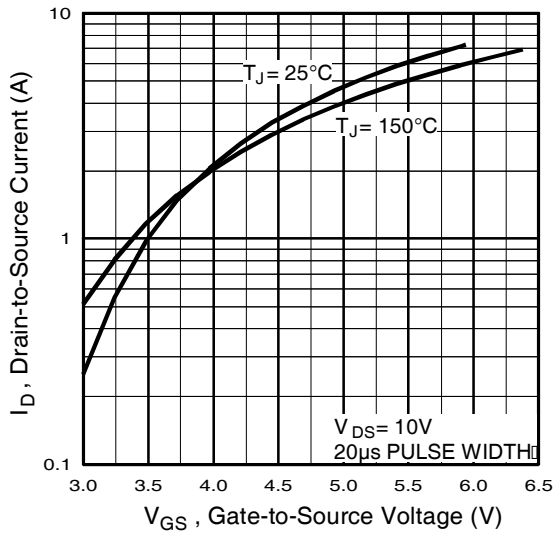


Fig 3. Typical Transfer Characteristics

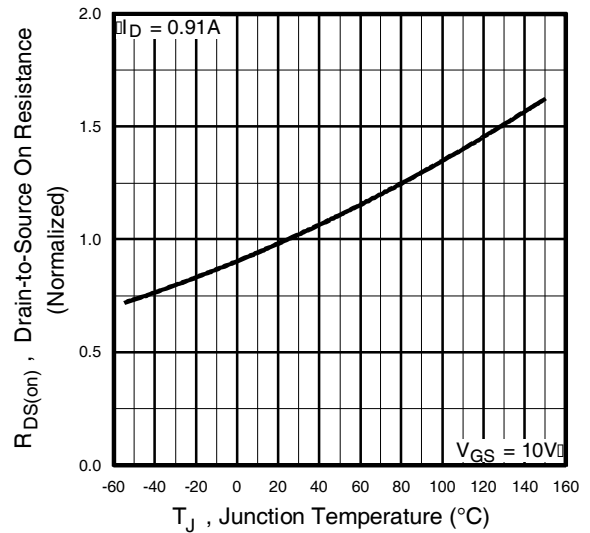


Fig 4. Normalized On-Resistance Vs. Temperature

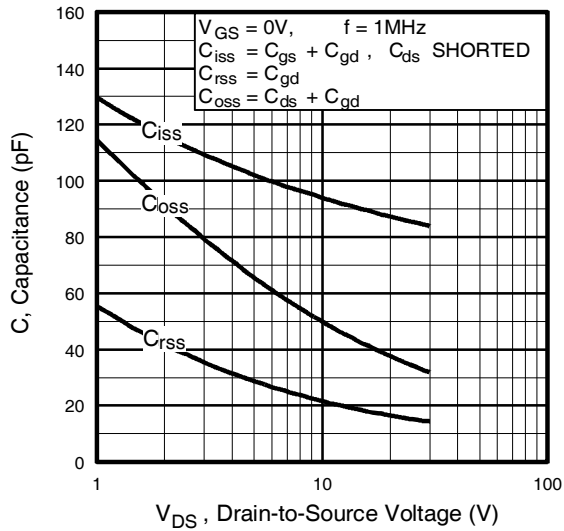


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

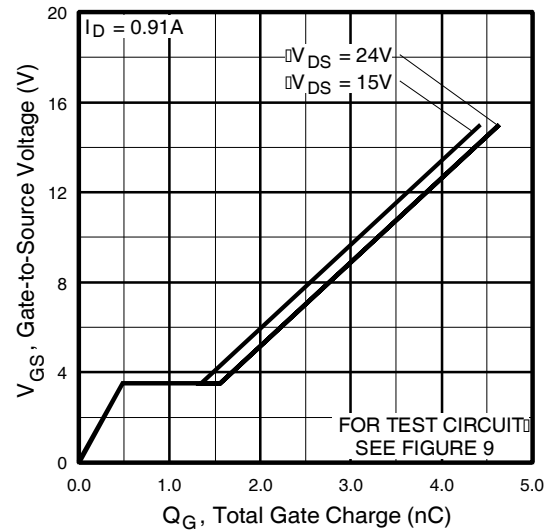


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

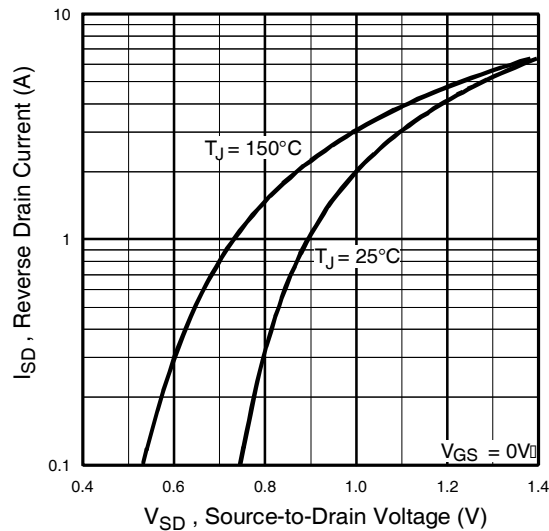


Fig 7. Typical Source-Drain Diode Forward Voltage

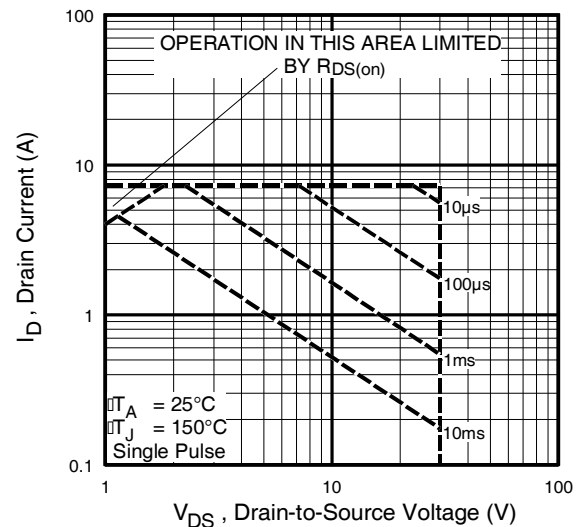


Fig 8. Maximum Safe Operating Area

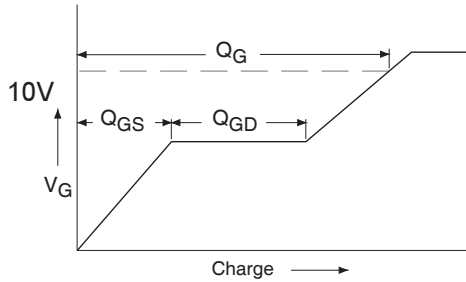


Fig 9a. Basic Gate Charge Waveform

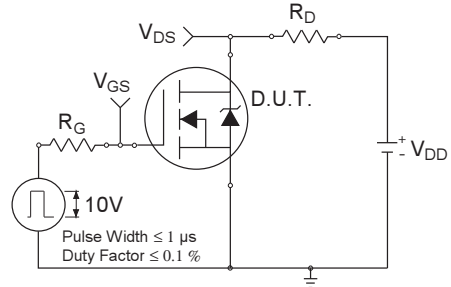


Fig 10a. Switching Time Test Circuit

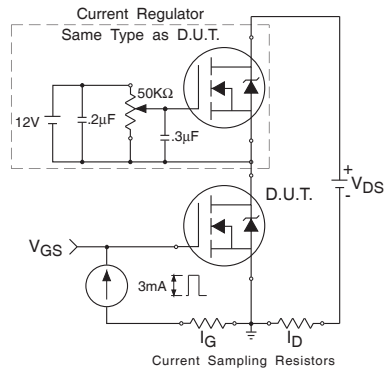


Fig 9b. Gate Charge Test Circuit

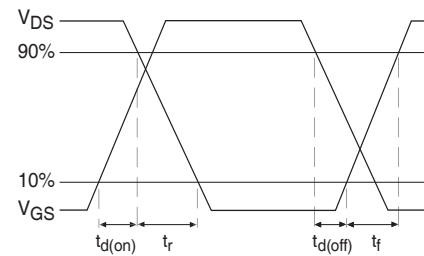


Fig 10b. Switching Time Waveforms

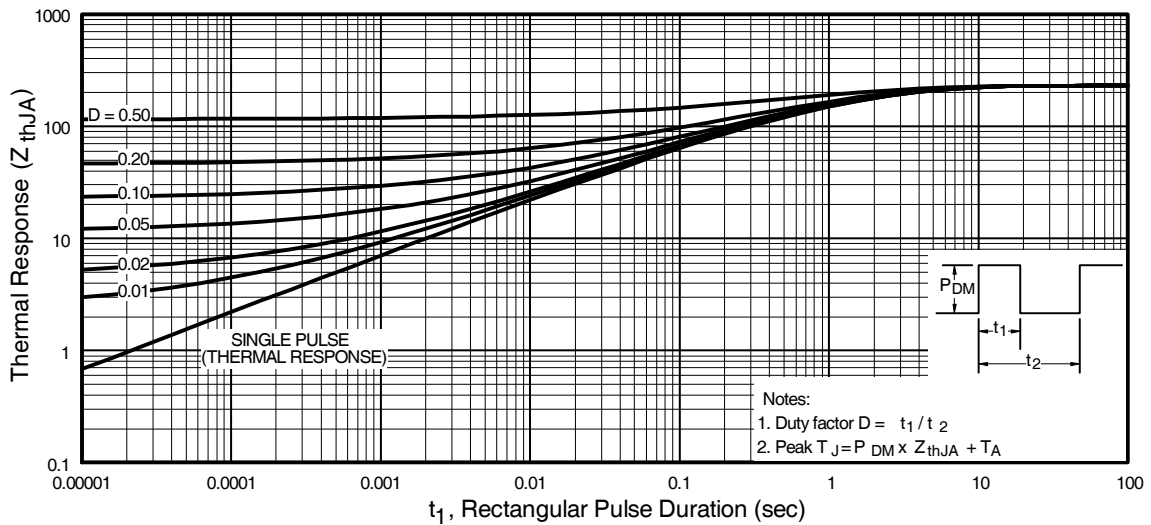


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

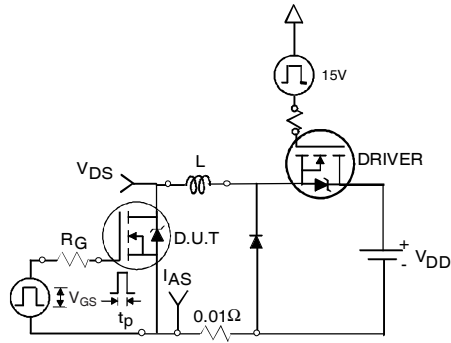


Fig 12a. Unclamped Inductive Test Circuit

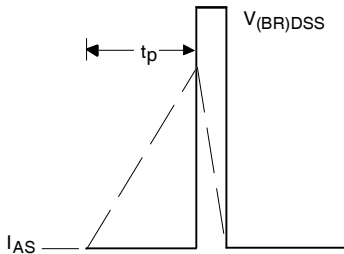


Fig 12b. Unclamped Inductive Waveforms

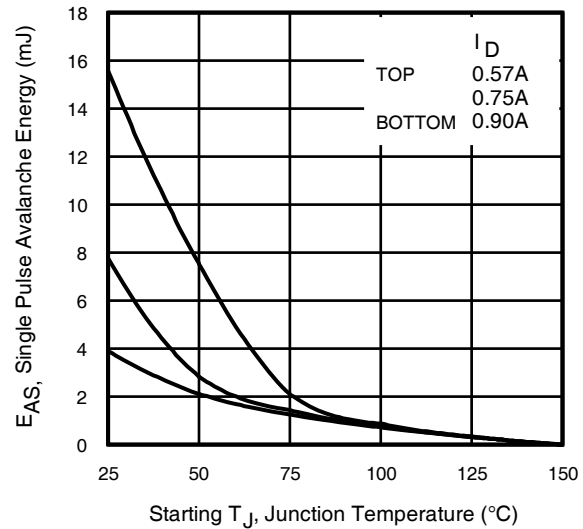
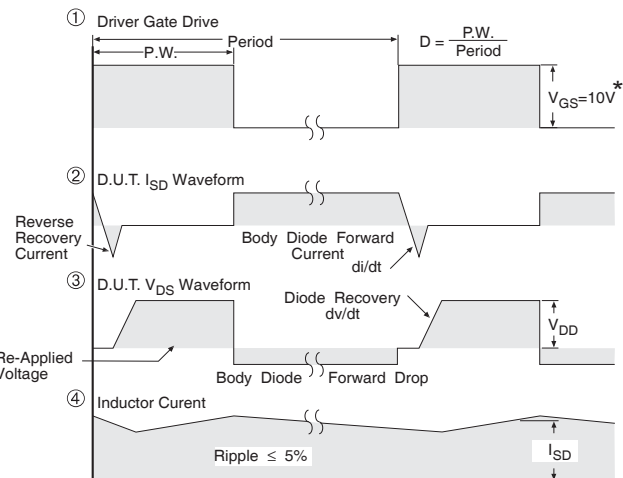
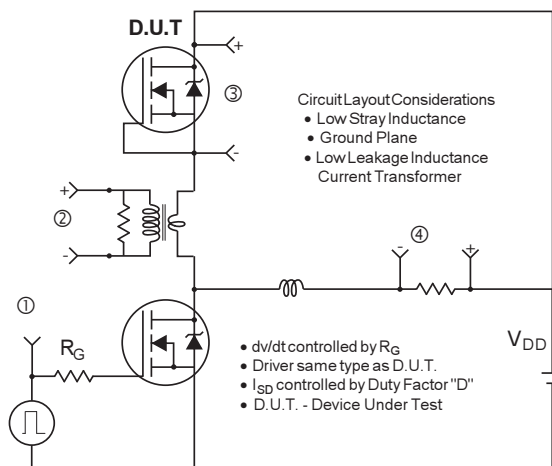


Fig 12c. Maximum Avalanche Energy vs. Drain Current

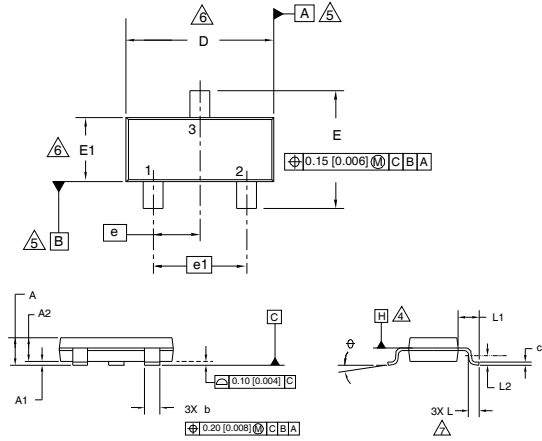


* $V_{GS} = 5V$ for Logic Level Devices

Fig 13. Peak Diode Recovery dv/dt Test Circuit for N-Channel HEXFET® Power MOSFETs

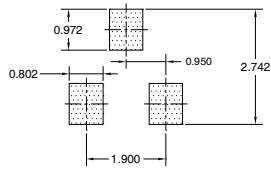
Micro3 (SOT-23) (Lead-Free) Package Outline

Dimensions are shown in millimeters (inches)



| DIMENSIONS | | | | |
|------------|-------------|------|--------|-------|
| SYMBOL | MILLIMETERS | | INCHES | |
| | MIN | MAX | MIN | MAX |
| A | 0.89 | 1.12 | 0.035 | 0.044 |
| A1 | 0.01 | 0.10 | 0.0004 | 0.004 |
| A2 | 0.88 | 1.02 | 0.035 | 0.040 |
| b | 0.30 | 0.50 | 0.012 | 0.020 |
| c | 0.08 | 0.20 | 0.003 | 0.008 |
| D | 2.80 | 3.04 | 0.110 | 0.120 |
| E | 2.10 | 2.64 | 0.083 | 0.104 |
| E1 | 1.20 | 1.40 | 0.047 | 0.055 |
| e | 0.95 | BSC | 0.037 | BSC |
| e1 | 1.90 | BSC | 0.075 | BSC |
| L | 0.40 | 0.60 | 0.016 | 0.024 |
| L1 | 0.54 | REF | 0.021 | REF |
| L2 | 0.25 | BSC | 0.010 | BSC |
| ⌀ | 0 | 8 | 0 | 8 |

Recommended Footprint

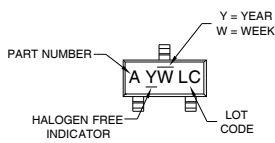


NOTES:

1. DIMENSIONING & TOLERANCING PER ANSI Y14.5M-1994
2. DIMENSIONS ARE SHOWN IN MILLIMETERS (INCHES).
3. CONTROLLING DIMENSION: MILLIMETER.
4. DATUM PLANE H IS LOCATED AT THE MOLD PARTING LINE.
5. DATUM A AND B TO BE DETERMINED AT DATUM PLANE H.
6. DIMENSIONS D AND E1 ARE MEASURED AT DATUM PLANE H. DIMENSIONS DOES NOT INCLUDE MOLD PROTRUSIONS OR INTERLEAD FLASH. MOLD PROTRUSIONS OR INTERLEAD FLASH SHALL NOT EXCEED 0.25 MM (0.010 INCH) PER SIDE.
7. DIMENSION L IS THE LEAD LENGTH FOR SOLDERING TO A SUBSTRATE.
8. OUTLINE CONFORMS TO JEDEC OUTLINE TO-236 AB.

Micro3 (SOT-23 / TO-236AB) Part Marking Information

Micro3 / SOT-23 Package Marking



PART NUMBER CODE REFERENCE:

- A = IRLML2402
- B = IRLML2803
- C = IRLML2402
- D = IRLML5103
- E = IRLML6402
- F = IRLML6401
- G = IRLML2502
- H = IRLML5203

Note: A line above the work week (as shown here) indicates Lead-free

W = (1-26) IF PRECEDED BY LAST DIGIT OF CALENDAR YEAR

| YEAR | Y | WORK WEEK | W |
|------|---|-----------|---|
| 2001 | 1 | 01 | A |
| 2002 | 2 | 02 | B |
| 2003 | 3 | 03 | C |
| 2004 | 4 | 04 | D |
| 2005 | 5 | | |
| 2006 | 6 | | |
| 2007 | 7 | | |
| 2008 | 8 | | |
| 2009 | 9 | | |
| 2010 | 0 | 24 | X |
| | | 25 | Y |
| | | 26 | Z |

W = (27-52) IF PRECEDED BY A LETTER

| YEAR | Y | WORK WEEK | W |
|------|---|-----------|---|
| 2001 | A | 27 | A |
| 2002 | B | 28 | B |
| 2003 | C | 29 | C |
| 2004 | D | 30 | D |
| 2005 | E | | |
| 2006 | F | | |
| 2007 | G | | |
| 2008 | H | | |
| 2009 | J | | |
| 2010 | K | 50 | X |
| | | 51 | Y |
| | | 52 | Z |

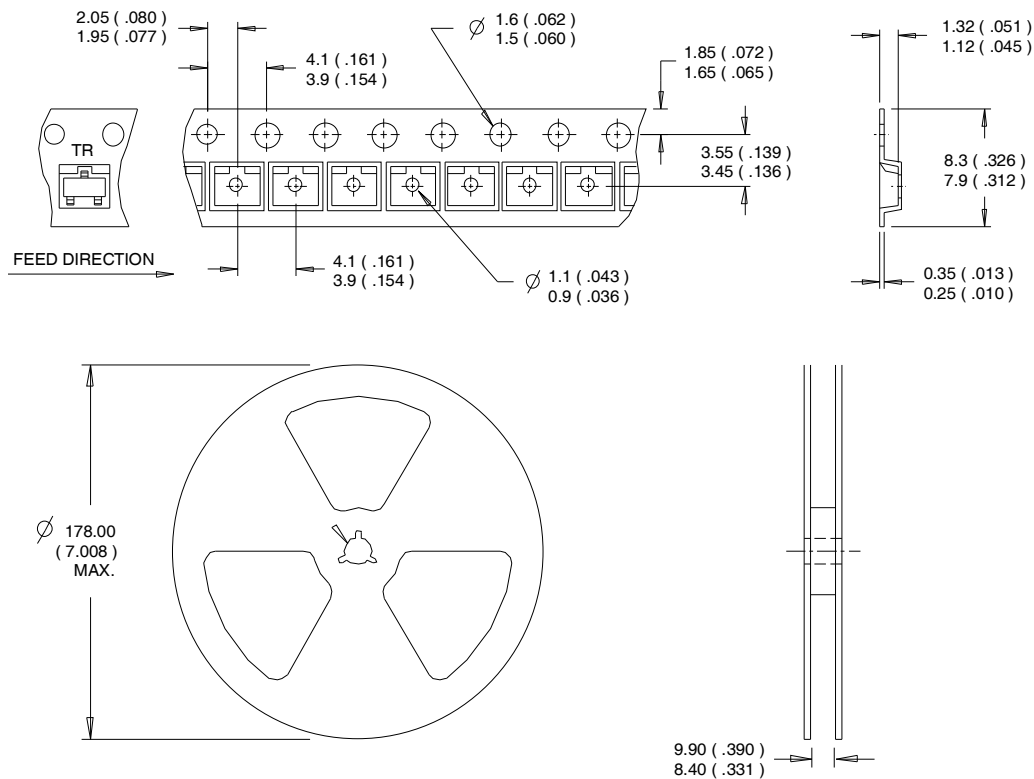
Note: For the most current drawing please refer to IR website at <http://www.irf.com/package>
www.irf.com

IRLML2803GPbF

International
IR Rectifier

Micro3™ Tape & Reel Information

Dimensions are shown in millimeters (inches)



NOTES:

1. CONTROLLING DIMENSION : MILLIMETER.
2. OUTLINE CONFORMS TO EIA-481 & EIA-541.

Note: For the most current drawing please refer to IR website at <http://www.irf.com/package>

Data and specifications subject to change without notice.

International
IR Rectifier

IR WORLD HEADQUARTERS: 101N.Sepulveda Blvd, El Segundo, California 90245, USA Tel: (310) 252-7105
TAC Fax: (310) 252-7903

Visit us at www.irf.com for sales contact information. 12/2011

www.irf.com

IMPORTANT NOTICE

The information given in this document shall in no event be regarded as a guarantee of conditions or characteristics ("Beschaffheitsgarantie").

With respect to any examples, hints or any typical values stated herein and/or any information regarding the application of the product, Infineon Technologies hereby disclaims any and all warranties and liabilities of any kind, including without limitation warranties of non-infringement of intellectual property rights of any third party.

In addition, any information given in this document is subject to customer's compliance with its obligations stated in this document and any applicable legal requirements, norms and standards concerning customer's products and any use of the product of Infineon Technologies in customer's applications.

The data contained in this document is exclusively intended for technically trained staff. It is the responsibility of customer's technical departments to evaluate the suitability of the product for the intended application and the completeness of the product information given in this document with respect to such application.

For further information on the product, technology, delivery terms and conditions and prices please contact your nearest Infineon Technologies office (www.infineon.com).

WARNINGS

Due to technical requirements products may contain dangerous substances. For information on the types in question please contact your nearest Infineon Technologies office.

Except as otherwise explicitly approved by Infineon Technologies in a written document signed by authorized representatives of Infineon Technologies, Infineon Technologies' products may not be used in any applications where a failure of the product or any consequences of the use thereof can reasonably be expected to result in personal injury.

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for [MOSFET](#) category:

Click to view products by [Infineon](#) manufacturer:

Other Similar products are found below :

[614233C](#) [648584F](#) [IRFD120](#) [JANTX2N5237](#) [FCA20N60_F109](#) [FDZ595PZ](#) [2SK2545\(Q,T\)](#) [405094E](#) [423220D](#) [TPCC8103,L1Q\(CM](#)
[MIC4420CM-TR](#) [VN1206L](#) [614234A](#) [715780A](#) [NTNS3166NZT5G](#) [SSM6J414TU,LF\(T](#) [751625C](#) [BUK954R8-60E](#) [GROUP A 5962-](#)
[8877003PA](#) [NTE6400](#) [SQJ402EP-T1-GE3](#) [2SK2614\(TE16L1,Q\)](#) [2N7002KW-FAI](#) [DMN1017UCP3-7](#) [EFC2J004NUZTDG](#) [ECH8691-TL-W](#)
[FCAB21350L1](#) [P85W28HP2F-7071](#) [DMN1053UCP4-7](#) [NTE221](#) [NTE222](#) [NTE2384](#) [NTE2903](#) [NTE2941](#) [NTE2945](#) [NTE2946](#) [NTE2960](#)
[NTE2967](#) [NTE2969](#) [NTE2976](#) [NTE6400A](#) [NTE2910](#) [NTE2916](#) [NTE2956](#) [NTE2911](#) [DMN2080UCB4-7](#) [TK10A80W,S4X\(S](#)
[SSM6P69NU,LF](#) [DMP22D4UFO-7B](#) [DMN1006UCA6-7](#)